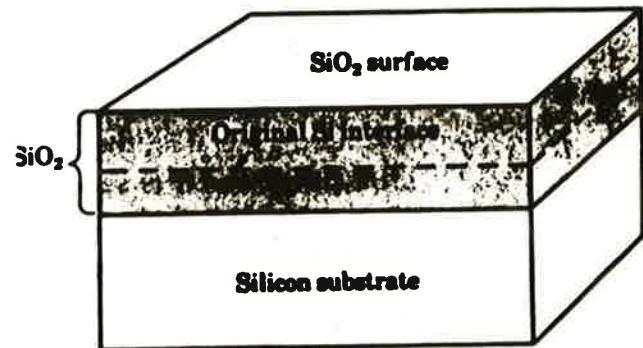


FIGURE 34.5
Growth of silicon dioxide, showing
consumption of silicon. Source: S. M.
Sze.



DRY OR WET OXIDATION
1650-2200°F
O₂-RICH ATM.

WATER VAPOR (STEAM)
HIGHER GROWTH RATE BUT
LOWER QUALITY

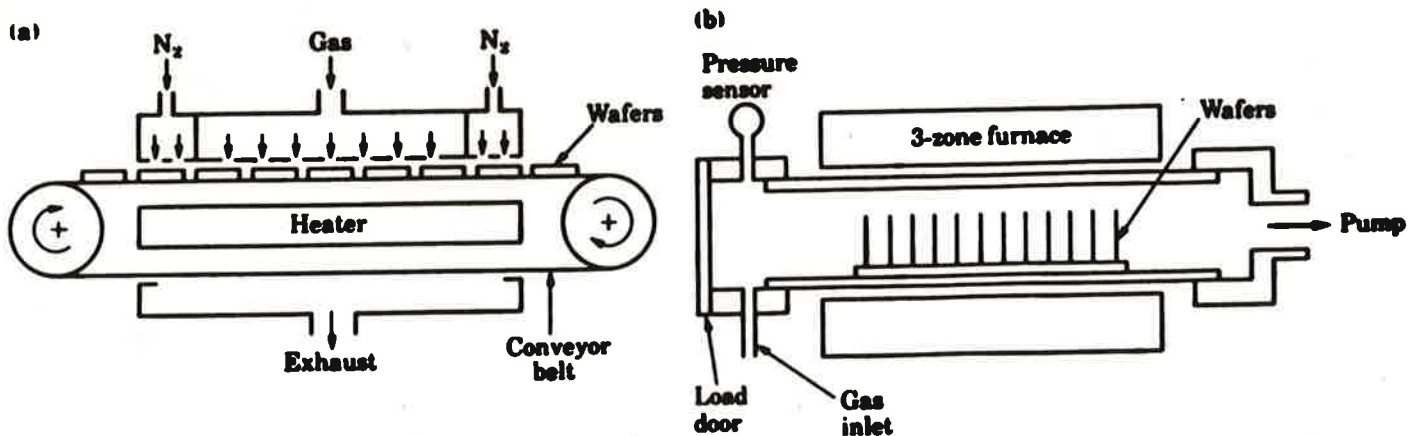


FIGURE 34.4
Schematic diagrams of (a) continuous, atmospheric-pressure CVD reactor and (b) low-pressure CVD. Source: S. M.
Sze.

